

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP321, TLP321-2, TLP321-4

PROGRAMMABLE CONTROLLERS

DC-OUTPUT MODULE

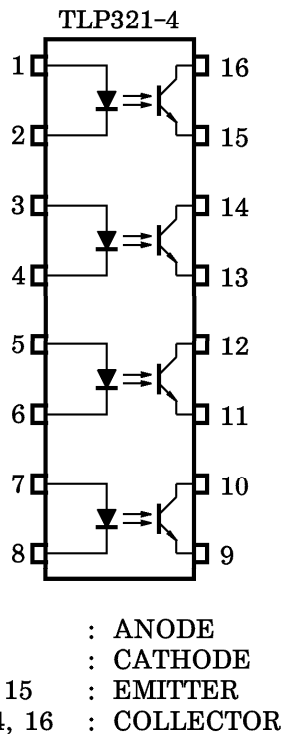
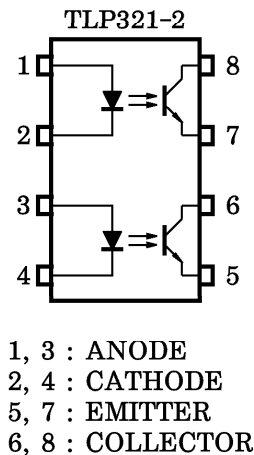
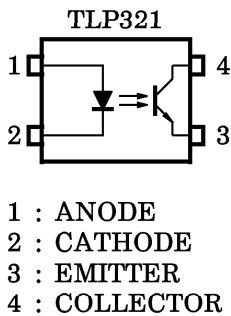
TELECOMMUNICATION

The TOSHIBA TLP321, -2 and -4 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP321-2 offers two isolated channels in an eight lead plastic DIP package, while the TLP321-4 provides four isolated channels in a sixteen plastic DIP package.

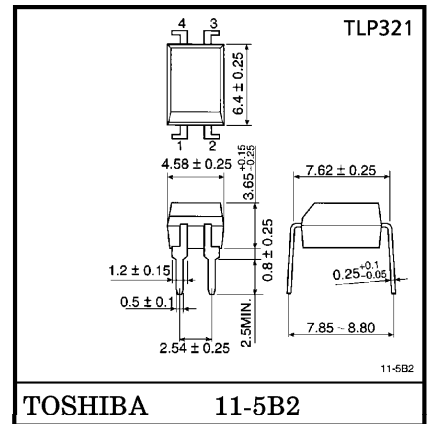
TLP321/-2/-4 have high V_{CEO} Voltage ($V_{CEO} = 80V$).

- Collector-Emitter Voltage : 80V (Min.)
- Current Transfer Ratio : 50% (Min.)
Rank GB : 100% (Min.)
- Isolation Voltage : 5000Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

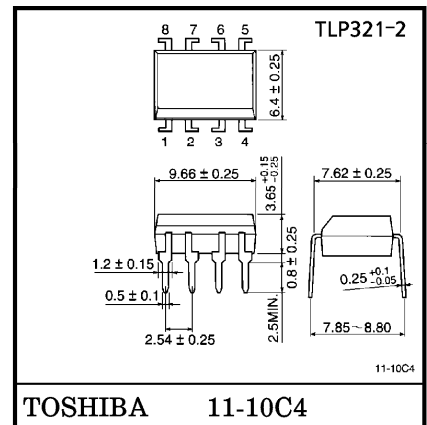
PIN CONFIGURATIONS (TOP VIEW)



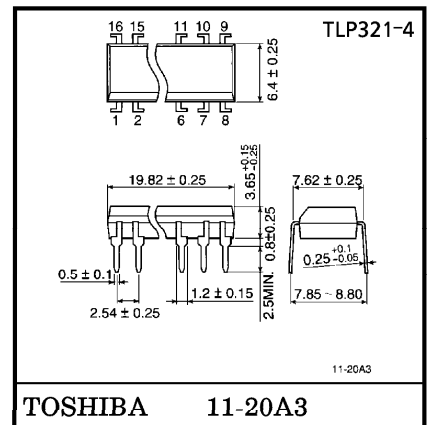
Unit in mm



Weight : 0.26g



Weight : 0.54g



Weight : 1.1g

CURRENT TRANSFER RATIO

TYPE	CLASSI- FICATION *1	CURRENT TRANSFER RATIO (%) (I_C / I_F)		MARKING OF CLASSIFICATION
		$I_F = 5\text{mA}$, $V_{CE} = 5\text{V}$, $T_a = 25^\circ\text{C}$		
		MIN.	MAX.	
TLP321	(None)	50	600	BLANK, Y, Y■, G, G■, B, B■, GB
	Rank Y	50	150	Y, Y■
	Rank GR	100	300	G, G■
	Rank BL	200	600	B, B■
	Rank GB	100	600	G, G■, B, B■, GB
TLP321-2	(None)	50	600	BLANK, GR, BL, GB
TLP321-4	Rank GB	100	600	GR, BL, GB

*1 : Ex. Rank GB : TLP321 (GB)

(Note) Application type name for certification test, please use standard product type name, i.e.

TLP321 (GB) : TLP321

TLP321-2 (GB) : TLP321-2

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			TLP321-1	TLP321-2 TLP321-4	
LED	Forward Current	I _F	60	50	mA
	Forward Current Derating	$\Delta I_F / ^\circ\text{C}$	-0.7 (Ta $\geq$ 39°C)	-0.5 (Ta $\geq$ 25°C)	mA / °C
	Pulse Forward Current	I _{FP}	1 (100 μ s pulse, 100pps)		A
	Reverse Voltage	V _R	5		V
	Junction Temperature	T _j	125		°C
DETECTOR	Collector-Emitter Voltage	V _{CEO}	80		V
	Emitter-Collector Voltage	V _{ECO}	7		V
	Collector Current	I _C	50		mA
	Collector Power Dissipation (1 Circuit)	P _C	150	100	mW
	Collector Power Dissipation Derating (1 Circuit, Ta $\geq$ 25°C)	$\Delta P_C / ^\circ\text{C}$	-1.5	-1.0	mW / °C
	Junction Temperature	T _j	125		°C
Storage Temperature Range		T _{stg}	-55~125		°C
Operating Temperature Range		T _{opr}	-55~100		°C
Lead Soldering Temperature		T _{sol}	260 (10s)		°C
Total Package Power Dissipation		R _T	250	150	mW
Total Package Power Dissipation Derating (Ta $\geq$ 25°C)		$\Delta P_T / ^\circ\text{C}$	-2.5	-1.5	mW / °C
Isolation Voltage (Note 1)		BV _S	5000 (AC, 1 min., RH $\leq$ 60%)		Vrms

(Note 1) Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{CC}	—	12	48	V
Forward Current	I_F	—	16	20	mA
Collector Current	I_C	—	1	10	mA
Operating Temperature	T_{opr}	-25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	80	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 48\text{V}$	—	10	100	nA
			$V_{CE} = 48\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Capacitance (Collector to Emitter)	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF

COUPLED ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F(\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$	—	—	0.4	V
		$I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

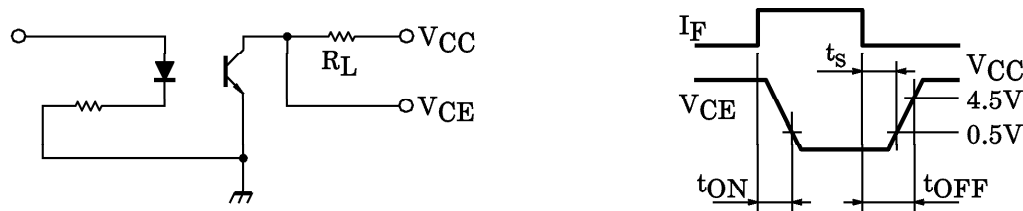
ISOLATION CHARACTERISTICS (Ta = 25°C)

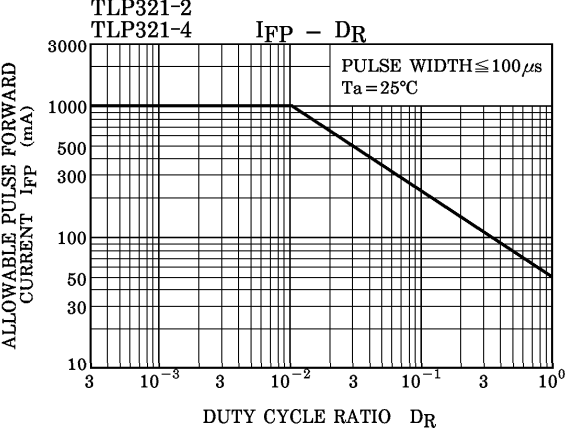
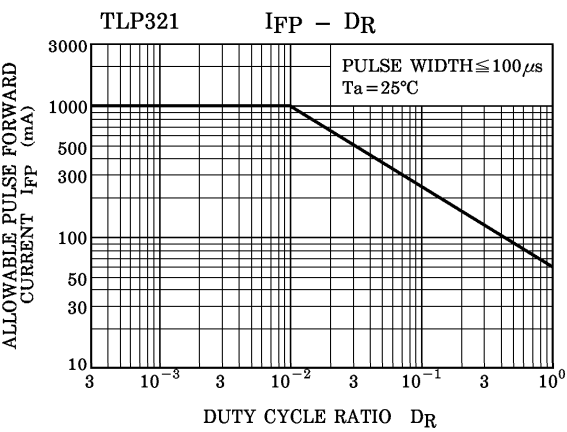
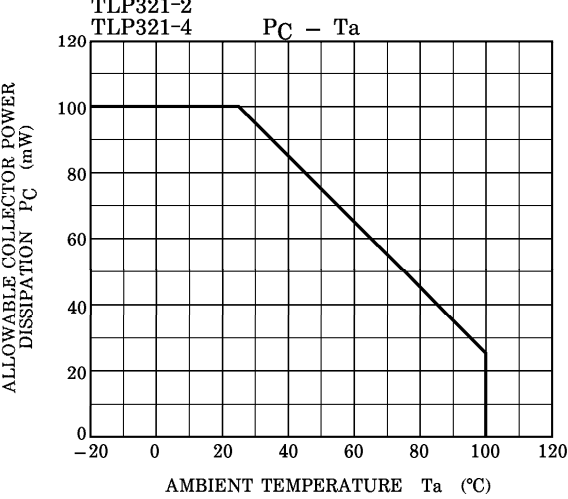
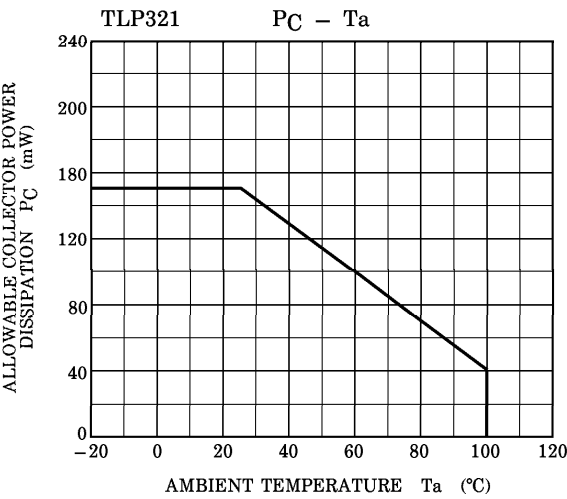
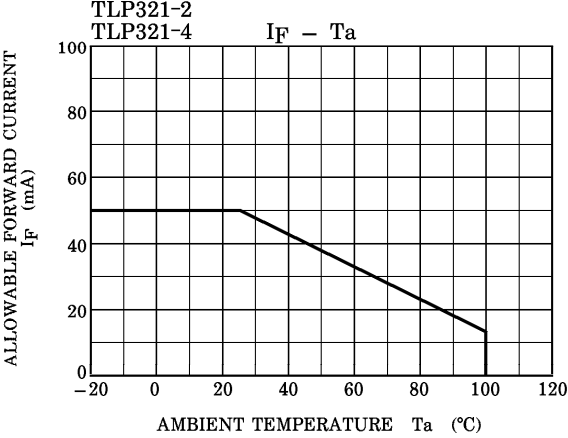
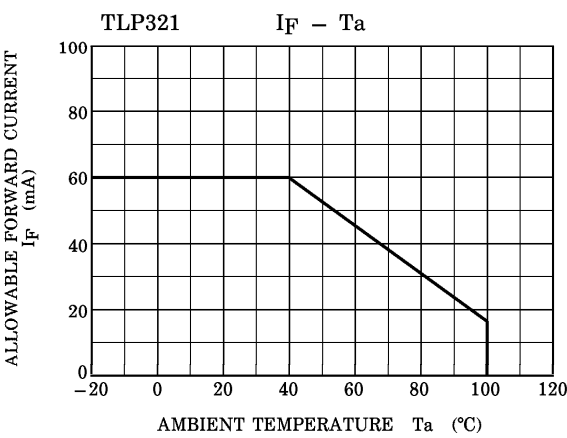
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	CS	VS=0, f=1MHz	—	0.8	—	pF
Isolation Resistance	RS	VS=500V, R.H.≦60%	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation Voltage	BVS	AC, 1 minute	5000	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc

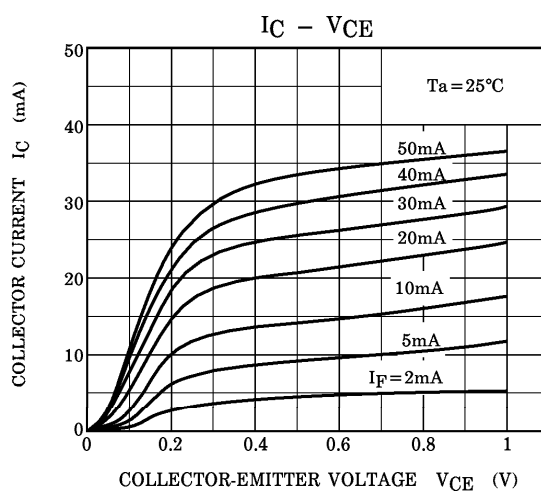
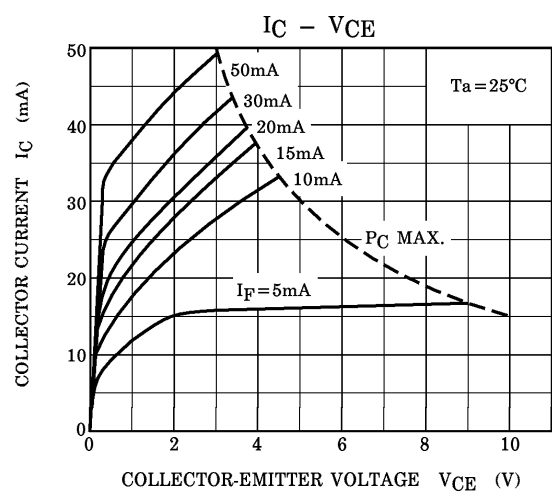
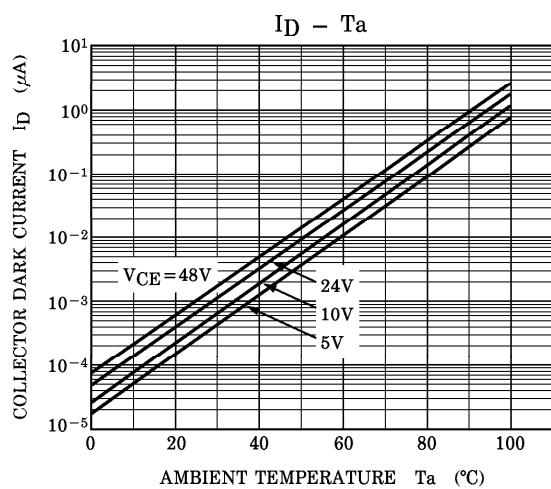
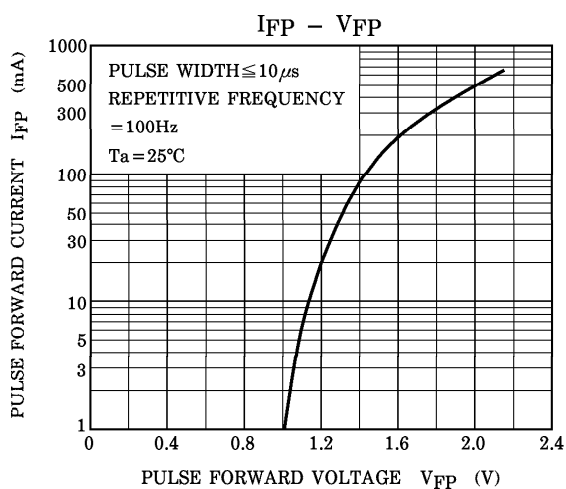
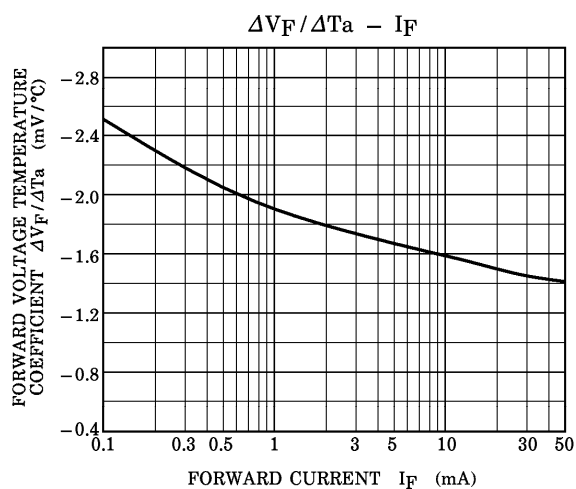
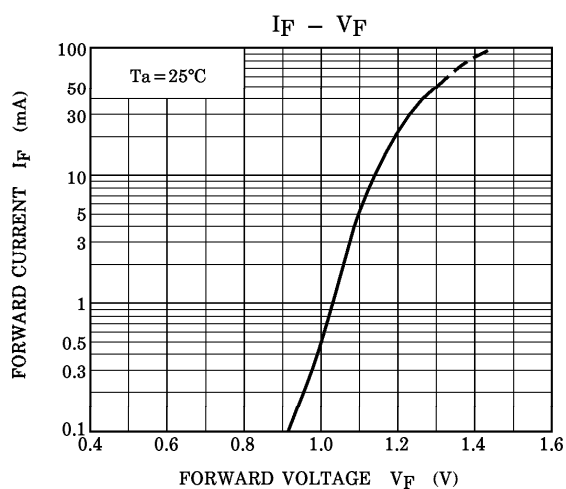
SWITCHING CHARACTERISTICS (Ta = 25°C)

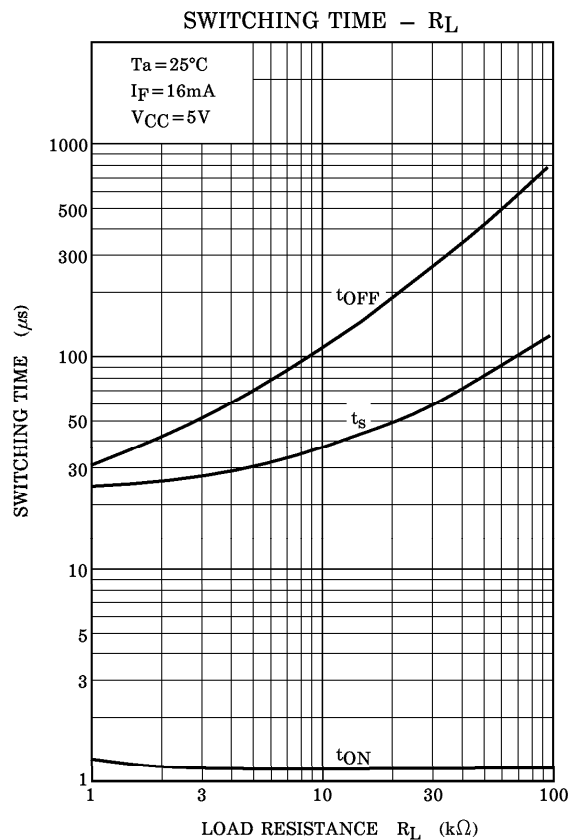
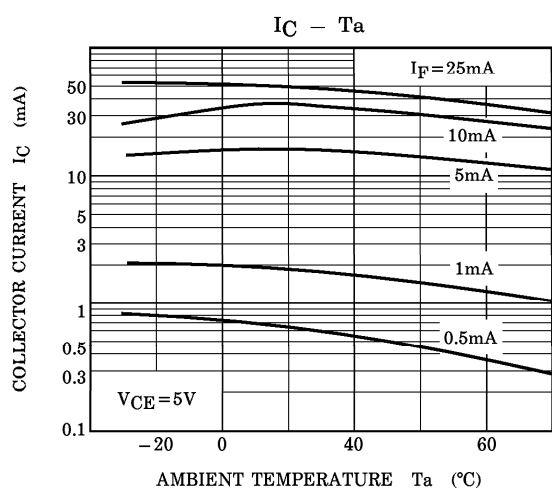
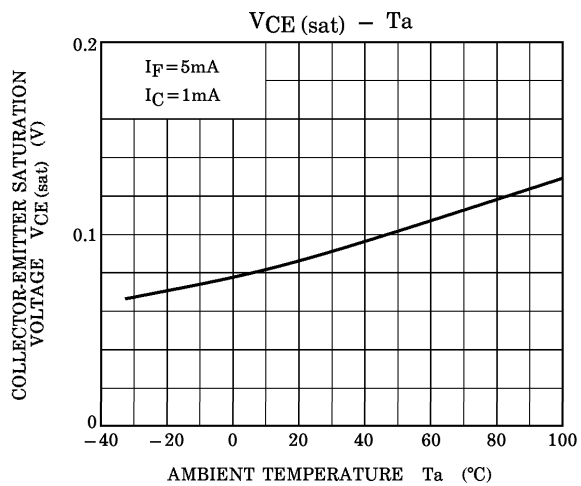
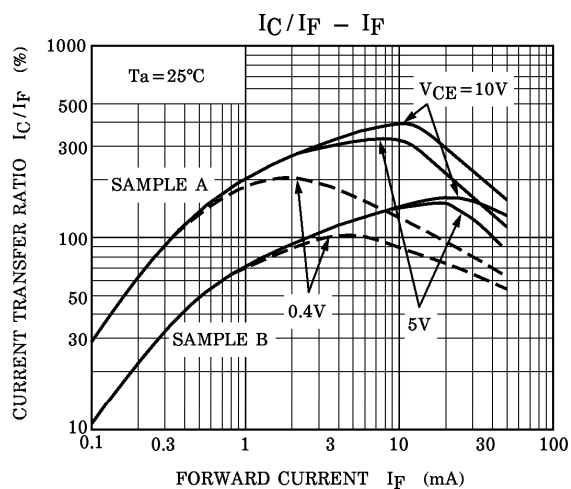
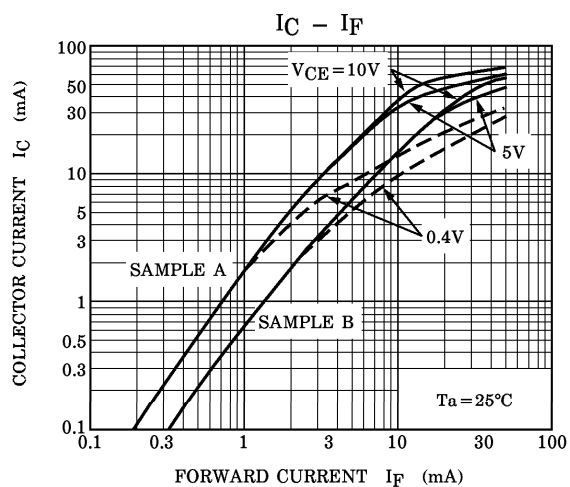
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr	VCC=10V IC=2mA RL=100Ω	—	2	—	μs
Fall Time	tf		—	3	—	
Turn-on Time	ton		—	3	—	
Turn-off Time	toff		—	3	—	
Turn-on Time	tON	RL=1.9kΩ (Fig.1) VCC=5V, IF=16mA	—	2	—	μs
Storage Time	ts		—	15	—	
Turn-off Time	tOFF		—	25	—	

Fig.1 Switching Time Test Circuit









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000707EBC

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